



SSCT12V11L3

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Single-Line ESD Protection Array

● Description

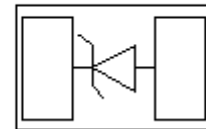
The SSCT12V11L3 Series is designed with AF technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium.

It has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD(electrostatic discharge), and EFT (electrical fast transients).

● Feature

- ✧ Single-channel ESD protection
- ✧ Peak Power Dissipation-1800W(8*20us Waveform)
- ✧ Replacement for MLV
- ✧ Protects I/O Port
- ✧ Low Clamping Voltage
- ✧ Low Leakage
- ✧ Response Time is <1ns
- ✧ RoHS Compliant
- ✧ Meets MSL 1 Requirements
- ✧ Reliable silicon device avalanche breakdown Structure

● PIN configuration



DFN1610-2L

● Applications

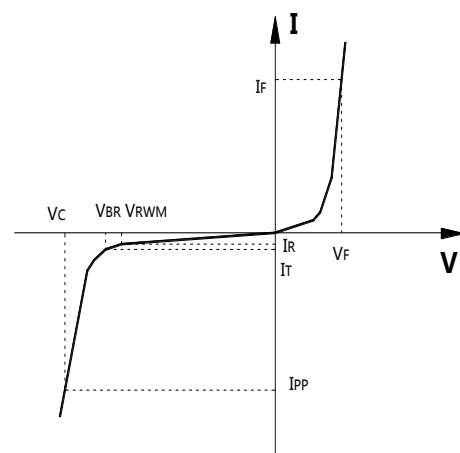
- ✧ Cell phone handsets and accessories
- ✧ Personal Digital Assistants
- ✧ Portable Instrumentation
- ✧ Digital Cameras
- ✧ Power supply protection
- ✧ Other electronics equipments communication systems

● Protection solution to meet

- ✧ IEC61000-4-2(ESD) ±30Kv(contact), ±30kV(air)
- ✧ IEC61000-4-4(EFT) 40A(5/50ns)

● Electronic Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PPP}	Peak Pulse Power
C	Junction Capacitance





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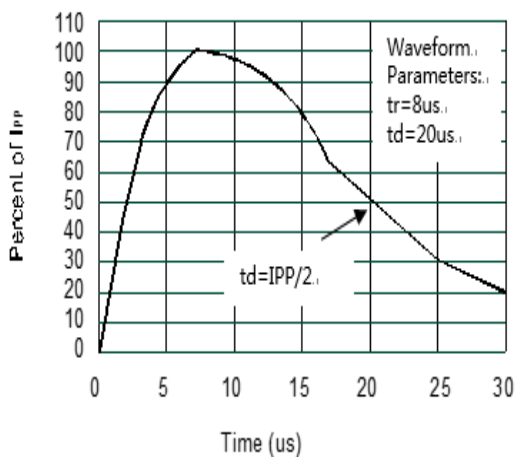
- **Absolute maximum rating @TA=25°C**

Symbol	Parameter	Value	Units
ESD	ESD Rating per IEC61000-4-2:Contact Air	30	KV
		30	
P _{PPP}	Peak Pulse Power (8/20μS)	1890	W
T _{STG}	Storage Temperature	-55/+150	°C
T _J	Operating Temperature	-55/+125	°C

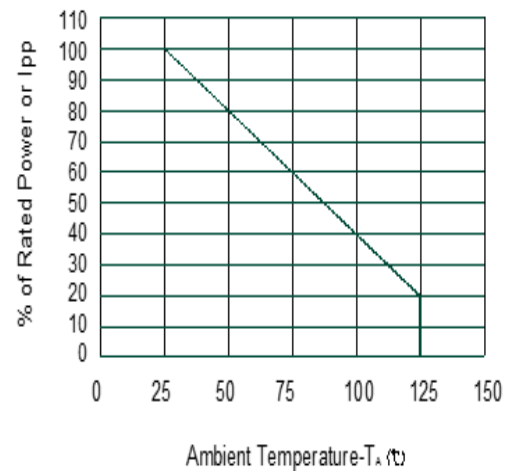
- **Electrical Characteristics @TA=25°C**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}	Any I/O to Ground		12		V
Breakdown Voltage	V _{BR}	I _t = 1mA Any I/O to Ground	13			V
Reverse Leakage Current	I _R	V _{RWM} = 12V, T = 25°C			1	μA
Clamping Voltage	V _{C1}	I _{PP} = 10A, t _P = 8/20μs		16.9		V
Clamping Voltage	V _{C2}	I _{PP} = 60A, t _P = 8/20μs		24		V
Junction Capacitance	C _J	V _R = 0V, f = 1MHz, any I/O pin to Ground		410		pF
Peak pulse current	I _{pp}	Any I/O to Ground			60	A
Peak Pulse Power	P _{PPP}	Peak Pulse Power (8/20 μ S)			1890	W

- **Typical Performance Characteristics**



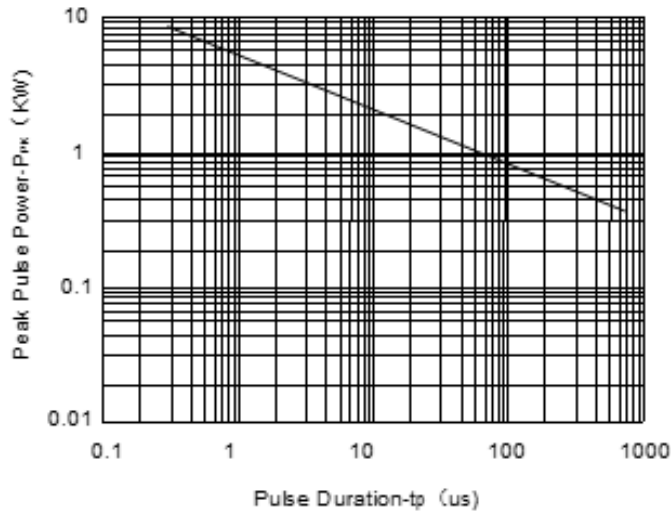
Pulse Waveform¹⁾



Power Derating Curve¹⁾

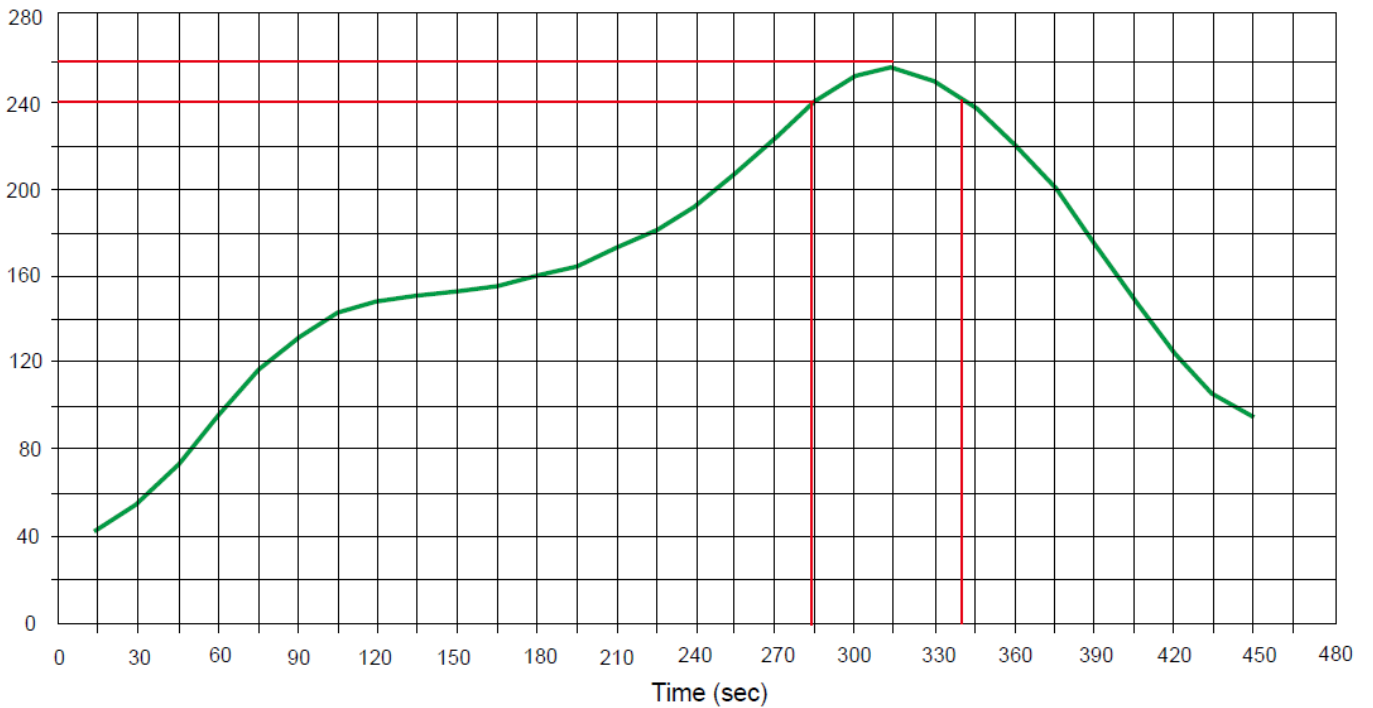


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Non-Repetitive Peak Pulse Power vs. Pulse Time

Peak Temp=257°C, Ramp Rate=0.802deg. °C/sec





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- Package Information

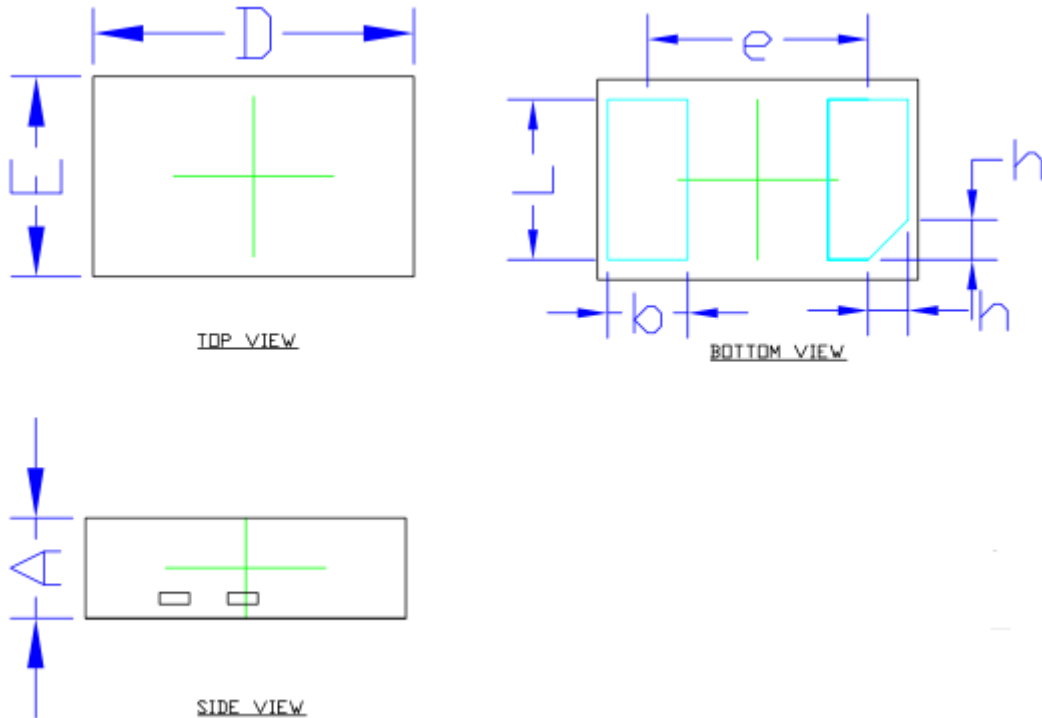
Ordering Information

Device	Marking	Package	Qty per Reel	Reel Size
SSCT12V11L3	12P	DFN1610-2L	10000	7 Inch

Mechanical Data

Case: DFN1610-2L

Case Material: Molded Plastic. UL Flammability



COMMON DIMENSION (MM)			
PKG	DFN1610		
REF.	MIN.	NOM.	MAX
A	0.45	0.50	0.55
D	1.55	1.60	1.65
E	0.95	1.00	1.05
b	0.35	0.40	0.45
L	0.75	0.80	0.85
e	1.10BSC		
h	0.15	0.20	0.25



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